Day 3 Hands-on: Bandstructures, metals and XC functionals

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Today's Themes:

- 1) Performing band structure calculations
- 1) DFT calculations for metals: smearing parameters
- XC functionals: LDA and PBE

Topics of the session

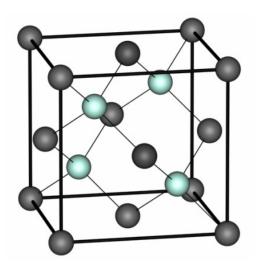
- 1. Performing band structure calculation
- 2. Performing metallic calculation: smearing
- 3. Exchange correlation functional

Exercise 1

Performing band structure calculations, example for Silicon and Aluminum

To compute the band structure of Silicon, go to folder:

ASESMA2025/Day3/example1.bandstructure/ex1.Si



```
&CONTROL
calculation = 'scf'.
&SYSTEM
ibrav = 2,
celldm(1) = 10.2,
nat = 2
ntyp = 1,
ecutwfc = 20.
&FL FCTRONS
ATOMIC_SPECIES
Si 28.086 Si.pbe-rrkj.UPF
ATOMIC_POSITIONS
          0.00. 0.00. 0.00
Si
          0.25. 0.25
                     0.25
K_POINTS automatic
666 000
```

1. Exercise 1: Band structure of Silicon

The scheme to compute the bands is the following:

Perform the SCF Calculation: Use pw.x to calculate the density (calculation = 'scf')

```
pw.x -in si.scf.in > si.scf.out
```

- Perform a bands- type NSCF Calculation: Use pw.x to with:
 - calculation = 'bands'
 - number of bands (variable nbnd) to be computed (if nothing is specified, the default is used)
 - a suitable path of k-points in specified K-POINTS card. The k-point path must be continuos in k-space.
- Calculate Bands datafile: Use bands.x, which, among others, produces data-files for the plot.
- **Plot the bands**: Use gnuplot to plot the band structures store in the file bands.dat.gnu.

Important: we must keep the prefix same outdir and prefix for "nscf" and "scf" pw.x and for the bands.x calculations!

Perform a bands- type NSCF Calculation: : Use pw.x to with calculation= 'bands'

pw.x -in si.bands.in> si.bands.out

Input file for band calculation looks like this:

```
&CONTROL
                                  ATOMIC SPECIES
  calculation='bands'
                                    Si 28.086 Si.pbe-rrkj.UPF ...
  prefix = 'Si'.
  pseudo_dir = '../../pseudo'
                                  ATOMIC_POSITIONS alat
  outdir='./tmp'
                                    Si 0.00 0.00 0.00
&SYSTEM
                                    Si 0.25 0.25 0.25
  ibrav = 2.
  celldm(1) = 10.262.
                                  K_POINTS {crystal_b}
  nat = 2
                                   6
  ntyp = 1,
  ecutwfc = 12.0.
                                   0.50 0.25 0.75 30 !W
  ecutrho = 200.0,
                                   0.00 0.00 0.00 30
  nbnd = 10
                                   0.50 0.00 0.50 30
                                   0.50 0.25 0.75 30
&FLECTRONS
                                   0.50 0.50 0.50 30
                                   0.00 0.00 0.00 30 !G
```

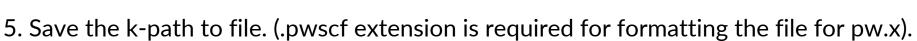
1. Exercise 1: Band structure of Silicon

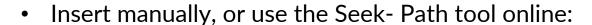
How to specify the k-path for band structure calculation:

- Use the k-path selection tool of xcrysden:
 - 1. Open the file si.scf.in with xcrysden;
 - 2. Select: Tools \rightarrow k-path selection;
 - 3. Select the path by clicking on a sequence of

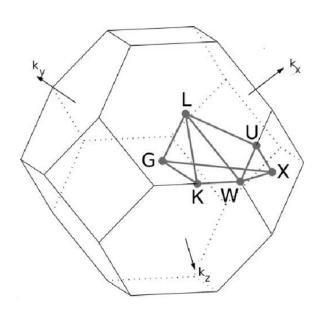
high-symmetry points:
$$W - \Gamma - X - W - L - \Gamma$$
;







https://www.materialscloud.org/work/tools/seekpath



 Calculate Bands datafile: Use bands.x, which, among others, produces data-files for the plot.

```
bands.x –in bands.in> bands.out
```

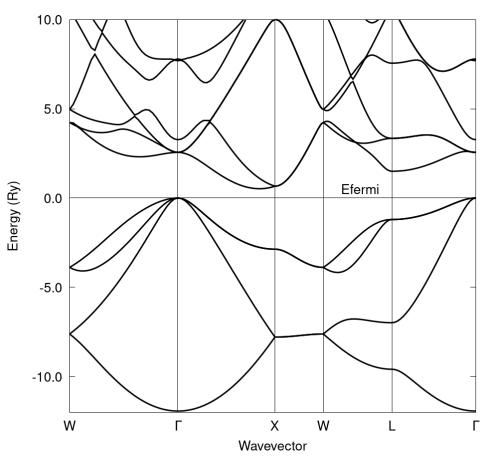
An input file for the data post processing program bands.x:

```
&BANDS
outdir = './tmp',
prefix='Si',
filband='bands.dat',
/
```

This program print the eigenvalues to the file specified in "filband". Bands data are stored in three files with different formats, among which we have bands.dat.gnu (can be plotted with gnuplot) and bands.dat can be visualized using the program plotband.x.

- Plot with gnuplot: run gnuplot plot_bands.gp
- The program plotband.x can be useful to obtain a postscript file of the band structure and a set of data files that can be plotted with xmgr. → type plotband.x on the terminal, which prompts the terminal input:

```
Input file > bands.dat
Reading 10 bands at 151 k-points
Range: -5.8760 17.7160eV Emin, Emax, [firstk, lastk] > -5.8760 17.7160
high-symmetry point: -1.0000 0.5000 0.0000 x coordinate 0.0000
high-symmetry point: 0.0000 0.0000 0.0000 x coordinate 1.1180
high-symmetry point: -1.0000 0.0000 0.0000 x coordinate 2.1180
high-symmetry point: -1.0000 0.5000 0.0000 x coordinate 2.6180
high-symmetry point: -0.5000 0.5000 0.5000 x coordinate 3.3251
high-symmetry point: 0.0000 0.0000 0.0000 x coordinate 4.1912
output file (gnuplot/xmgr) > si.bands.dat
bands in gnuplot/xmgr format written to file si.bands.dat
output file (ps) > bands.ps
Efermi > 6.0653
deltaE, reference E (for tics) 2, 6.0653
bands in PostScript format written to file bands.ps
```



Optional homework: can you calculate the DOS of Silicon?

1. Exercise 2: Aluminum

To compute the band structure of Silicon, go to folder:

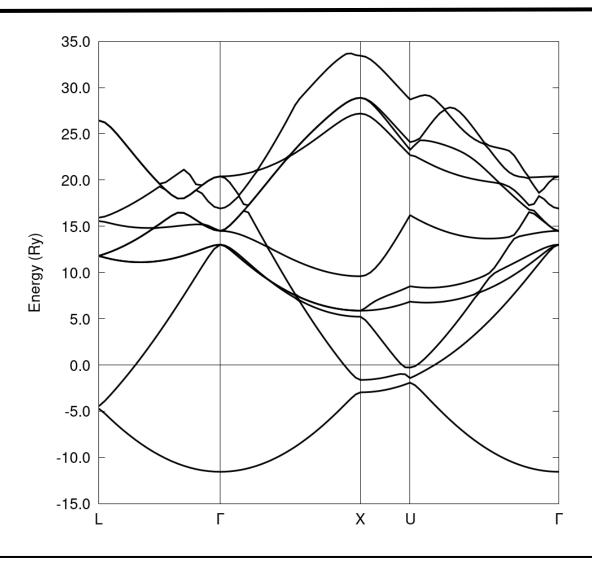
ASESMA2025/Day3/example1.bandstructure/ex2.Al

and use the same procedure for silicon:

- Self-consistent calculation (pw.x)
- Select a k-point path (i.e. by using XCrysDen, ...) and do "bands"-type non-SCF pw.x calculation
- Run a bands.x calculation
- Plot the results using gnuplot, or run plotband.x

Optional homework: converge the ecut_wfc and k-points for Aluminium, as done in Day2 (you find the scripts in folder *ex2.Al/convergence_test*)

1. Exercise 2: Aluminum



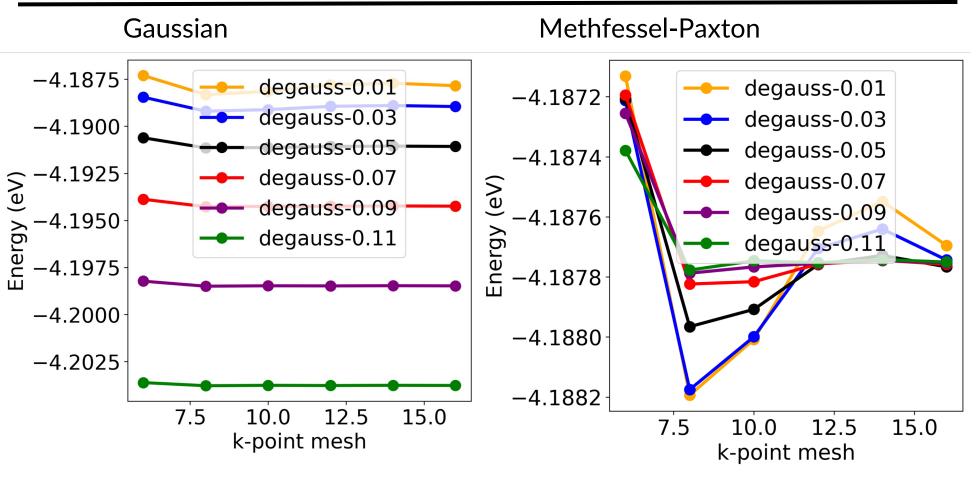
Exercise 2

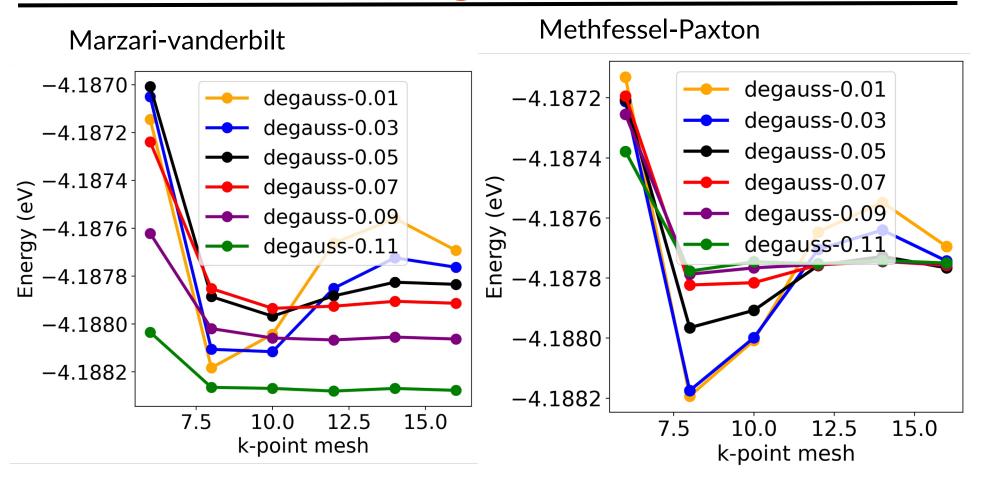
Performing metallic calculations: smearing

In this exercise we will compute the total energy for this fcc Al with the following values for degauss, k-point meshes and different smearing variables:

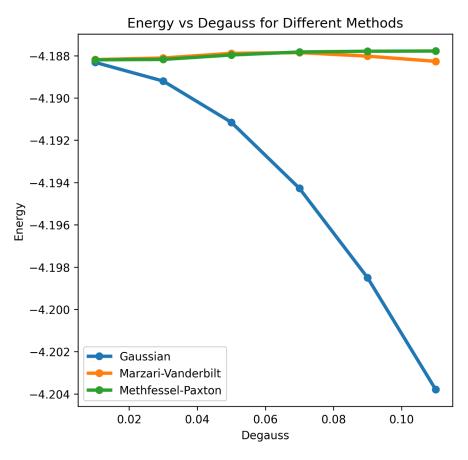
- degauss variable, in range from 0.01 to 0.11
- k-points: N×N×N (1×1×1) with N=6,8,10, ..., 16
- smearing variable, possible values: 'gauss' (or 'g'), 'marzari-vanderbilt'
- (or 'm-v'), 'methfessel-paxton' (or 'm-p')
- Follow the instructions in example2.smearing:

Plot the convergence of the total energy with respect to the number of k-points for the different smearing values.





Choose a suitable k-point mesh and plot the total energy as a function of degauss for Marzari-Vanderbilt and Gaussean smearing.



Exercise 3

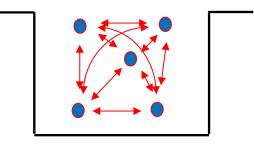
Exchange correlation functional

DAY 3: Exchange Correlational Functional

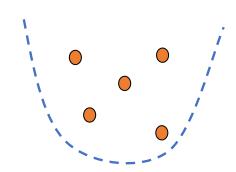
Go to the exercise 3 folder

cd ASESMA2025/Hands-on-basic/Day3/

Kohn-Sham DFT







- electron
- finteraction
- —— external potential $v_{ext}({f r})$

Kohn-Sham particles
 (non-interacting)
 effective potential $v_{KS}(\mathbf{r})$

$$\left[-\frac{\hbar^2}{2m_e} \nabla^2 + v_{KS}[n](\mathbf{r}) \right] \phi_i(\mathbf{r}) = \epsilon_i \phi_i(\mathbf{r})$$

$$v_{KS}[n](\mathbf{r}) = V_{ext}(\mathbf{r}) + e^2 \int d\mathbf{r}' \frac{n(\mathbf{r}')}{|\mathbf{r} - \mathbf{r}'|} + \frac{\delta E_{xc}[n]}{\delta n(\mathbf{r})}$$

LDA: The xc energy density of the inhomogeneous system in r is locally approximated with that of a homogeneous electron gas with density n(r)

$$E_{\rm xc}^{\rm LDA} = \int d\mathbf{r} \, n(\mathbf{r}) \varepsilon_{\rm xc}^{\rm HEG}(n(\mathbf{r}))$$

• LDA: The xc energy density of the inhomogeneous system in **r** is locally approximated with that of a homogeneous electron gas with density n(**r**)

$$E_{\rm xc}^{\rm LDA} = \int d\mathbf{r} \, n(\mathbf{r}) \varepsilon_{\rm xc}^{\rm HEG}(n(\mathbf{r}))$$

GGA: include the dependence on the gradient of the density

$$E_{\rm xc}^{\rm GGA} = \int d\mathbf{r} \, n(\mathbf{r}) \varepsilon_{\rm xc}(n(\mathbf{r}), \nabla n(\mathbf{r})) = \int d\mathbf{r} \, n(\mathbf{r}) \varepsilon_{\rm xc}^{\rm HEG}(n(\mathbf{r})) F_{\rm xc}(n(\mathbf{r}), \nabla n(\mathbf{r}))$$

• LDA: The xc energy density of the inhomogeneous system in **r** is locally approximated with that of a homogeneous electron gas with density n(**r**)

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 Meta-GGA: include the dependency on the laplacian of the density and kinetic energy density

$$E_{\rm xc}^{\rm mGGA} = \int d\mathbf{r} \, n(\mathbf{r}) \varepsilon_{\rm xc}(n(\mathbf{r}), \nabla n(\mathbf{r}), \nabla^2 n(\mathbf{r}), \tau) \qquad \tau = \frac{1}{2} \sum_i |\nabla \psi_i(\mathbf{r})|^2$$

LDA: The xc energy density of the inhomogeneous system in r is locally
approximated with that of a homogeneous electron gas with density n(r)

$$E_{\mathrm{xc}}^{\mathrm{LDA}} = \int d\mathbf{r} \, n(\mathbf{r}) \varepsilon_{\mathrm{xc}}^{\mathrm{HEG}}(n(\mathbf{r}))$$

GGA: include the dependence on the gradient of the density

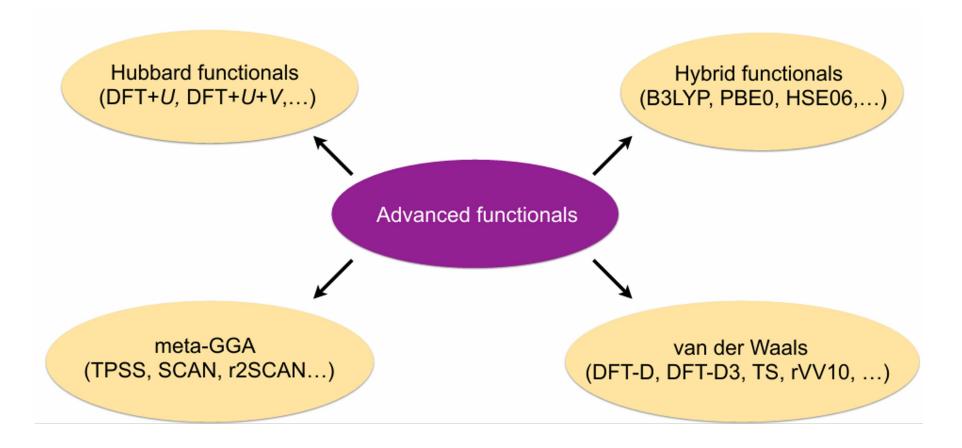
$$E_{\rm xc}^{\rm GGA} = \int d\mathbf{r} \, n(\mathbf{r}) \varepsilon_{\rm xc}(n(\mathbf{r}), \nabla n(\mathbf{r})) = \int d\mathbf{r} \, n(\mathbf{r}) \varepsilon_{\rm xc}^{\rm HEG}(n(\mathbf{r})) F_{\rm xc}(n(\mathbf{r}), \nabla n(\mathbf{r}))$$

 Meta-GGA: include the dependency on the laplacian of the density and kinetic energy density

$$E_{\rm xc}^{\rm mGGA} = \int d{\bf r} \, n({\bf r}) \varepsilon_{\rm xc}(n({\bf r}), \nabla n({\bf r}), \nabla^2 n({\bf r}), \tau) \qquad \tau = \frac{1}{2} \sum_i |\nabla \psi_i({\bf r})|^2$$
 Hybrid functionals: include a fraction of Fock exchange

 $E_{\rm xc}^{\rm hyb} = (1 - a_0)E_{\rm x}^{\rm DFT} + a_0E_{\rm x}^{\rm HF} + E_{\rm c}^{\rm DFT}$

Some advanced exchange-correlation functionals



Some drawbacks of LDA / GGA

Self-interaction errors

Consequences: - over delocalization of electrons (d and f)

- incorrect description of charge transfer
- incorrect energetics of chemical reactions
- underestimation of band gaps

- ...

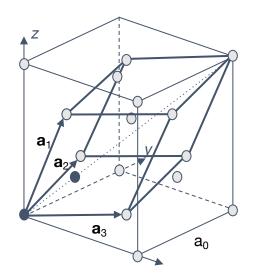
Lack of non-locality

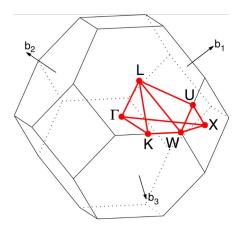
Consequences: - incorrect description of weak long-range (Van der Waals) interactions

- inadequate description of bond breaking and formation
- no Rydberg series

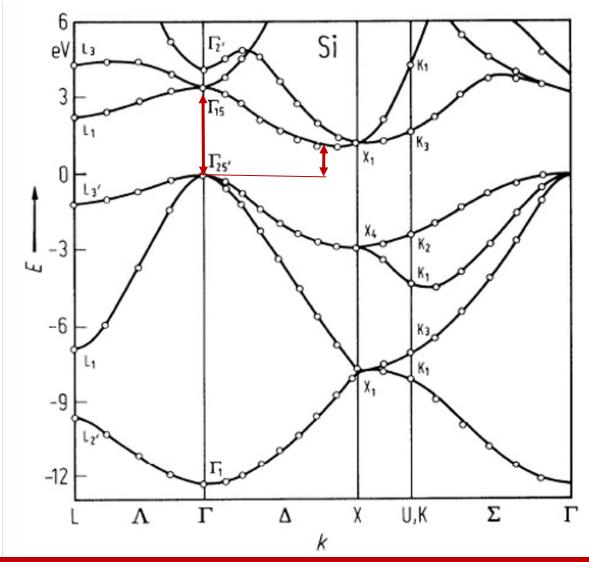
- ...

FCC Silicon

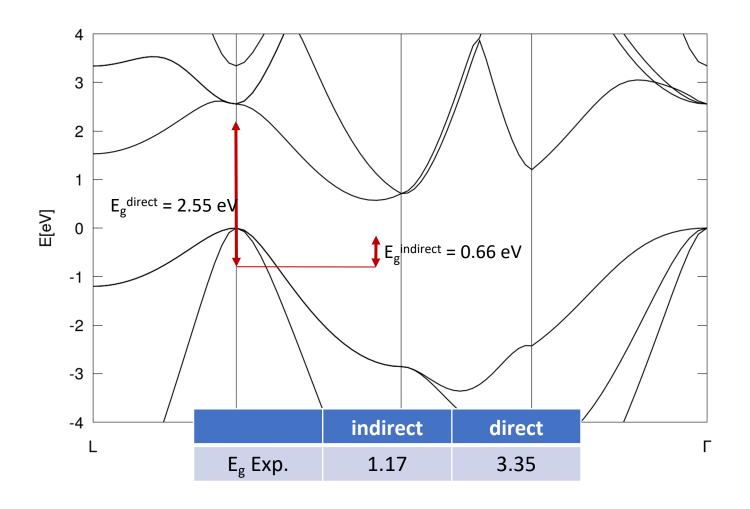




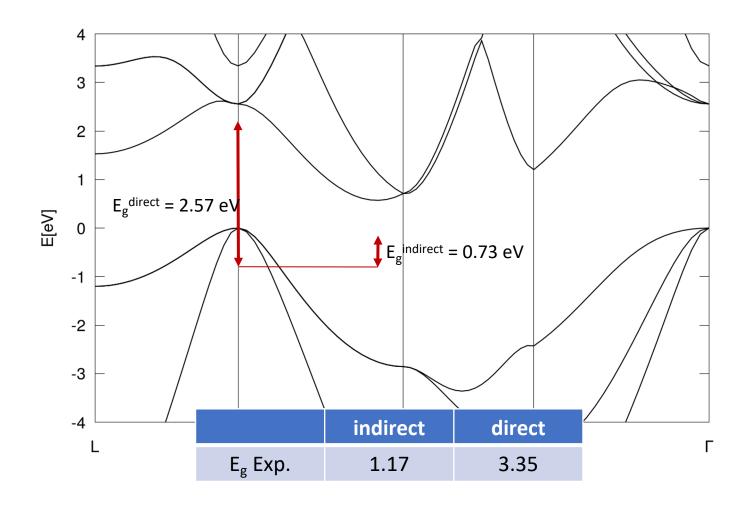




LDA Silicon band structure



GGA Silicon band structure



Silicon band Gap: summary

ecut = 20 Ry, k mesh: $6 \times 6 \times 6$

Functional	indirect Gap	Direct Gap	Band width
LDA	0.66	2.55	11.94
GGA	0.73	2.57	11.90
Exp.	1.17	3.35	12.5

Silicon Lattice Parameter: summary

ecut = 36 Ry, k mesh: $6 \times 6 \times 6$

Functional		
LDA	5.401	93.2
GGA	5.476	85.8
Exp.	5.431	90.0

Thank you!

Questions?